

U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.		Serial No.	
NOV 09 2004				M-15222 US		10/632,155	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant			
(Use several sheets if necessary)				Yi Ding			
				Filing Date		Group	
				July 30, 2003		2818	
U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
DA	AA	6,265,739	Jul. 2001	Yaegashi et al.			
	AB	6,747,310	Jun. 2004	Fan et al.			
	AC	2003/0205776	Nov. 2003	Yaegashi et al.			
	AD	6,468,865	Oct. 2002	Yang et al.			
	AE	6,218,689	Apr. 2001	Chang et al.			
	AF	6,214,669	Apr. 2001	Hisamune			
	AG	6,162,682	Dec. 2000	Kleine			
	AH	6,232,185	May-01	Wang			
	AI	5,912,843	Jun. 1999	Jeng			
	AJ	6,436,764	Aug. 2002	Hsieh			
	AK	6,344,993	5 Feb. 2002	Harari et al.			
	AL	5,668,757	Sept. 1997	Jeng			
	AM	6,355,524	Mar. 2002	Tuan et al.			
	AN	6,696,340	Feb. 2004	Furuhata			
	AO	5,705,415	Jan. 1998	Orlowski et al.			
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
	AW						
	AX						
	AY						
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Examiner		Date Considered		3/23/05			
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U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>Pa</i>	AA	5,445,983	Aug. 1995	Hong			
	AB	5,910,912	Jun. 1999	Hsu et al.			
	AC	5,918,124	Jun. 1999	Sung			
	AD	6,040,216	Mar. 2000	Sung			
	AE	6,107,141	Aug. 2000	Hsu et al.			
	AF	6,133,098	Oct. 2000	Ogura et al.			
	AG	6,187,636	Feb. 2001	Jeong			
	AH	6,228,695	May. 2001	Hsieh et al.			
	AI	6,294,297	Sep. 2001	Chen			
	AJ	6,436,764	Aug. 2002	Hsieh			
	AK	6,566,196	May-03	Haselden et al.			
	AL	6,635,533	Oct. 2003	Chang et al.			
	AM	6,642,103	Nov. 2003	Wils et al.			
	AN	6,660,589	Dec. 2003	Park			
	AO	6,803,276	Oct. 2004	Kim et al.			
	AP	5,633,185	May. 1997	Yiu et al.			
	AQ	5,821,143	Oct. 1998	Kim et al.			
<i>Pa</i>	AR	6,764,905	Jul. 2004	Jeng et al.			
	AS						
	AT						
	AU						
	AV						
	AW						
	AX						
	AY						
	AZ						
Examiner <i>SWR</i>		Date Considered <i>9/26/05</i>					
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				July 30, 2003		Unassigned	
U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>DL</i>	AA	6,420,231	16 Jul. 2002	Harari et al.	438	257	
<i>DL</i>	AB	2003/0218908 A1	27 Nov. 2003	Park et al.			
<i>DL</i>	AC	2004/0004863 A1	8 Jan. 2004	Wang			
	AD						
	AE						
	AF						
	AG						
	AH						
Foreign Patent Documents							
							Translation
		Document	Date	Country	Class	Subclass	Yes No
<i>DL</i>	AI	EP 0 938 098 A2	25 Aug. 1999	Europe			
	AJ						
	AK						
	AL						
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>DL</i>	AM	United States Patent Application No. 10/798,475, entitled "Fabrication of Conductive Lines Interconnecting Conductive Gates in Nonvolatile Memories and Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15296 US.					
<i>DL</i>	AN	United States Patent Application No. 10/797,972, entitled "Fabrication of Conductive Lines Interconnecting First Conductive Gates in Nonvolatile Memories Having Second Conductive Gates Provided By Conductive Gates Lines, Wherein The Adjacent Conductive Gate Lines For The Adjacent Columns Are Spaced From Each Other, And Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15297 US.					
	AO						
	AP						
Examiner <i>DL</i>		Date Considered <i>3/23/05</i>					
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